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## Photoemission of CsI-incorporated multilayer

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Photoemission of CsI was measured by varying the thickness of the CsI layer. After deposition of CsI, the sample was transferred to the next detection chamber via transfer rod without breaking the vacuum, enabling *in situ* photoemission measurement. A multilayer was positioned under the CsI layer to enhance the photoemission current. The morphology of the CsI layer was examined by scanning electron microscopy (SEM) and atomic force microscopy (AFM). The photoemission current was increased by increasing the thickness of CsI, however, showing the saturation behavior. The photoemission behavior will be further explained in the poster.